

## References

1. Brown, Paul M. Jr.; US Patent 4,228,367, “*High speed integrated switching circuit for analog signals*”, Issued: October 14, 1980
2. Zwanziger, Peter; US Patent 4,987,362, “*Self-regulating drive circuit for the base current of a power transistor with saturation level control*”, Issued: January 22, 1991
3. Williams, Richard K.; US Patent 5,909,103, “*Safety switch for lithium ion battery*”, Issued: June 1, 1999
4. Alwardi, Milad et. al.; US Patent 5,965,997, “*Battery monitoring circuit with storage of charge and discharge accumulation values accessible therefrom*”, Issued: October 12, 1999
5. Morrill, David P.; US Patent 6,249,148, “*Low power variable base drive circuit*”, Issued: June 19, 2001
6. MOXTEK™ Application Note “*Low Noise Junction Field Effect Transistors*”, Feb. ‘01
7. Technology and product information for JFET devices from Lovoltech Inc. at the following URL: <http://www.lovoltech.com/products.htm>

## Diagrams

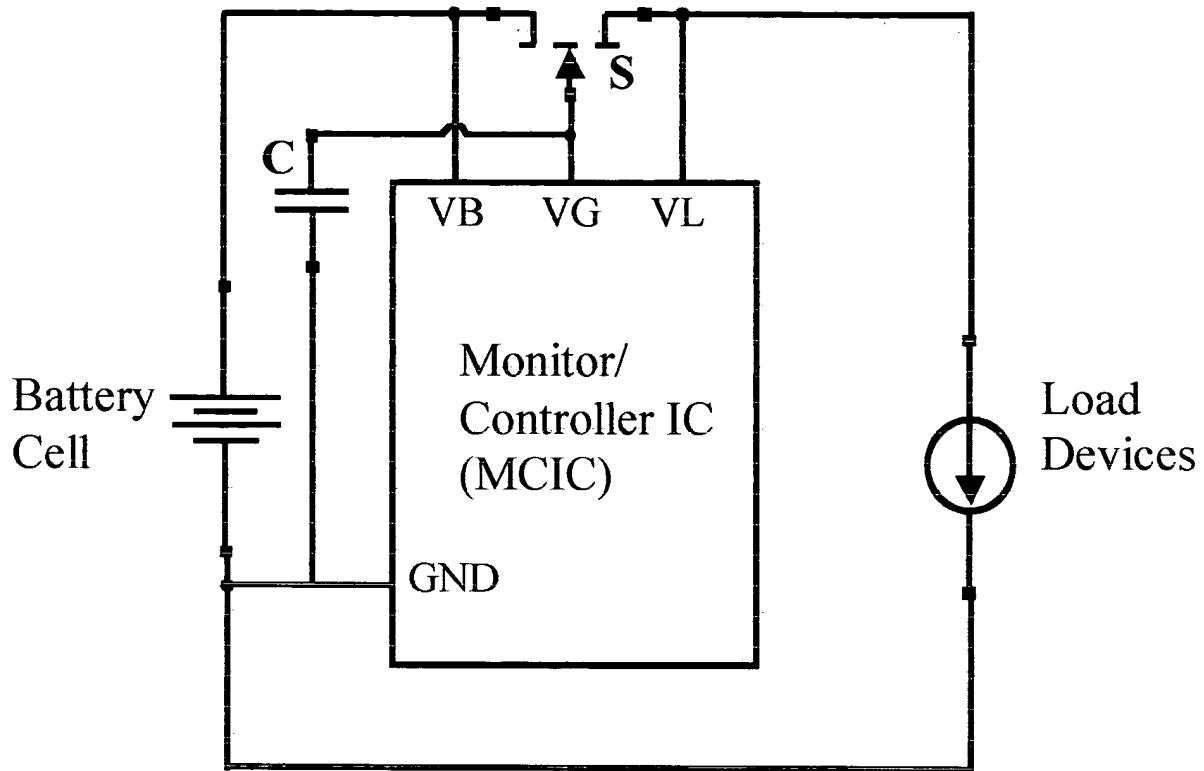


Fig. 1: One possible system-level embodiment of the invention

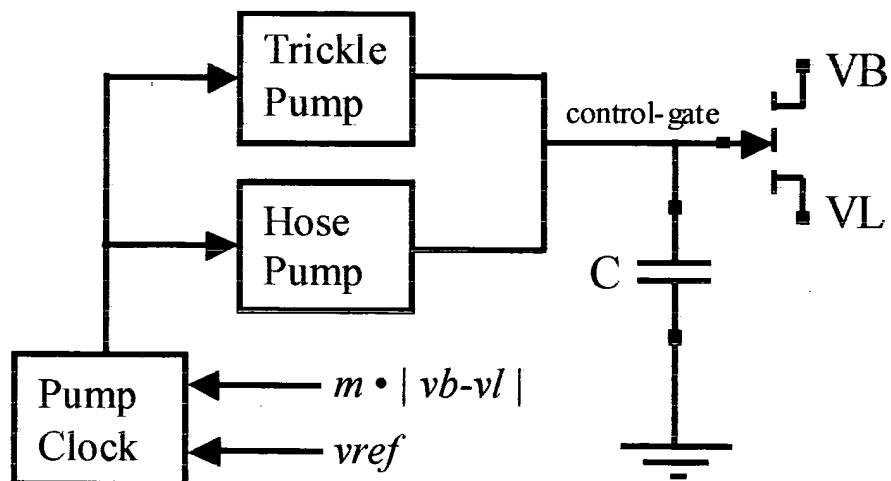


Fig. 2: An illustration of Variable-Current Drive and Dual-Function Capacitor

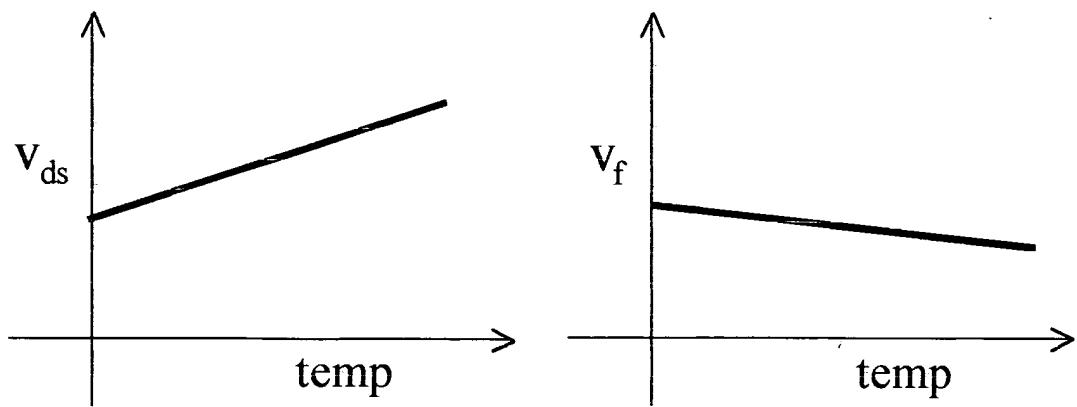


Fig. 3: Illustrations of channel and gate junction voltage drops of the switch